

## Features

- Optimized for a Multitude of Applications
- CW and Pulsed Operation: 50 W Output Power
- Internally Pre-matched
- 260°C Reflow Compatible
- 50 V Operation
- 100% RF Tested
- RoHS\* Compliant

## Applications

- military radio communications, digital cellular infrastructure, RF energy, avionics, test instrumentation and RADAR

## Description

The MAPC-A1110-AP is a high power GaN on Silicon HEMT D-mode amplifier optimized for DC - 2700 MHz frequency operation. The device supports both CW and pulsed operation with peak output power levels to 50 W (47 dBm) in a plastic package.

## Typical Performance:

Measured in Evaluation Test Fixture:  $P_{IN} = 32$  dBm, 100  $\mu$ s pulse width, 10% duty cycle

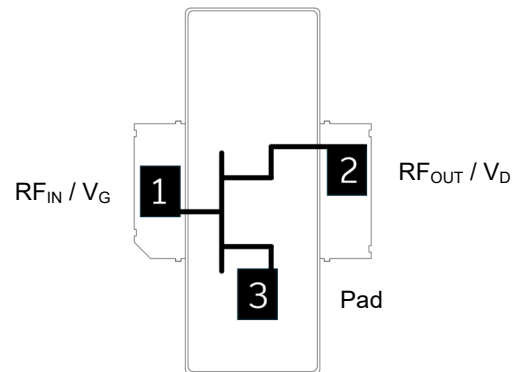
- $V_{DS} = 50$  V,  $I_{DQ} = 100$  mA,  $T_C = 25^\circ\text{C}$

Frequency (MHz)	Output Power (dBm)	Gain (dB)	$\eta_D$ (%)
2400	48.57	16.56	69
2450	48.63	16.63	72
2500	48.22	16.22	66



TO-272S-2

## Functional Schematic



## Pin Configuration

Pin #	Pin Name	Function
1	$RF_{IN} / V_G$	RF Input / Gate
2	$RF_{OUT} / V_D$	RF Output / Drain
3	Pad <sup>1</sup>	Ground / Source

1. The exposed pad centered on the package bottom must be connected to RF, DC and thermal ground.

## Ordering Information

Part Number	Package
MAPC-A1110-AP000	Bulk Quantity
MAPC-A1110-APTR1	Tape and Reel
MAPC-A1110-APSB1	Sample Board

\* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

**RF Electrical Characteristics:  $T_C = 25^\circ\text{C}$ ,  $V_{DS} = 50\text{ V}$ ,  $I_{DQ} = 100\text{ mA}$**

**Note: Performance in MACOM Application Fixture (2400 - 2500 MHz), 50  $\Omega$  system**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Small Signal Gain	CW, 2500 MHz	$G_{SS}$	-	18.8	-	dB
Power Gain	CW <sub>2</sub> , 2500 MHz, 2 dB Gain Compression	$G_{SAT}$	-	16.6	-	dB
Saturated Drain Efficiency	CW <sub>2</sub> , 2500 MHz, 2 dB Gain Compression	$\eta_{SAT}$	-	65	-	%
Saturated Output Power	CW <sub>2</sub> , 2500 MHz, 2 dB Gain Compression	$P_{SAT}$	-	48.1	-	dBm
Gain Variation (-40°C to +85°C)	Pulsed <sup>2</sup> , 2500 MHz	$\Delta G$	-	0.005	-	dB/°C
Power Variation (-40°C to +85°C)	Pulsed <sup>2</sup> , 2500 MHz	$\Delta P_{2dB}$	-	0.005	-	dB/°C
Gain	CW <sub>2</sub> , 2500 MHz, $P_{IN} = 32\text{ dBm}$	$G_P$	-	16.2	-	dB
Drain Efficiency	CW <sub>2</sub> , 2500 MHz, $P_{IN} = 32\text{ dBm}$	$\eta$	-	66	-	%
Ruggedness: Output Mismatch	All phase angles	$\Psi$	VSWR = 10:1, No Device Damage			

**RF Electrical Specifications:  $T_A = 25^\circ\text{C}$ ,  $V_{DS} = 50\text{ V}$ ,  $I_{DQ} = 100\text{ mA}$**

**Note: Performance in MACOM Production Test Fixture, 50  $\Omega$  system**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Power Gain	CW <sub>2</sub> , 2500 MHz, 2 dB Gain Compression	$G_{SAT}$	14.5	15.8	-	dB
Saturated Drain Efficiency	CW <sub>2</sub> , 2500 MHz, 2 dB Gain Compression	$\eta_{SAT}$	67	71	-	%
Saturated Output Power	CW <sub>2</sub> , 2500 MHz, 2 dB Gain Compression	$P_{SAT}$	49	49.8	-	dBm
Gain	CW, 2500 MHz, $P_{IN} = 33\text{ dBm}$	$G_P$	15.5	16.4	-	dB
Drain Efficiency	CW, 2500 MHz, $P_{IN} = 33\text{ dBm}$	$\eta$	63	69	-	%

2. Pulse details: 100  $\mu\text{s}$  pulse width, 1 ms period, 10% Duty Cycle.

**DC Electrical Characteristics  $T_A = 25^\circ\text{C}$**

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Units
Drain-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 130\text{ V}$	$I_{DLK}$	-	-	10.8	mA
Gate-Source Leakage Current	$V_{GS} = -8\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GLK}$	-	-	10.8	mA
Gate Threshold Voltage	$V_{DS} = 50\text{ V}$ , $I_D = 10.8\text{ mA}$	$V_T$	-2.6	-2.0	-1.6	V
Gate Quiescent Voltage	$V_{DS} = 50\text{ V}$ , $I_D = 250\text{ mA}$	$V_{GSQ}$	-2.4	-1.8	-1.4	V

## Absolute Maximum Ratings<sup>3,4,5,6,7</sup>

Parameter	Absolute Maximum
Drain Source Voltage, $V_{DS}$	130 V
Gate Source Voltage, $V_{GS}$	-10 to 3 V
Gate Current, $I_G$	10 mA
Storage Temperature Range	-65°C to +150°C
Case Operating Temperature Range	-40°C to +120°C
Channel Operating Temperature Range, $T_{CH}$	-40°C to +225°C
Absolute Maximum Channel Temperature	+250°C

3. Exceeding any one or combination of these limits may cause permanent damage to this device.
4. MACOM does not recommend sustained operation above maximum operating conditions.
5. Operating at drain source voltage  $V_{DS} < 55$  V will ensure  $MTTF > 2.5 \times 10^6$  hours.
6. Operating at nominal conditions with  $T_{CH} \leq 225^\circ\text{C}$  will ensure  $MTTF > 2.5 \times 10^6$  hours.
7. MTTF may be estimated by the expression  $MTTF \text{ (hours)} = A e^{[B + C/(T+273)]}$  where  $T$  is the channel temperature in degrees Celsius,  $A = 0.0355$ ,  $B = -9.89$ , and  $C = 13,925$ .

## Thermal Characteristics<sup>8</sup>

Parameter	Test Conditions	Symbol	Typical	Units
Thermal Resistance using Finite Element Analysis	$V_{DS} = 50$ V, $P_D = 30$ W, $T_C = 85^\circ\text{C}$ , $T_{CH} = 225^\circ\text{C}$	$R_{\theta}(\text{FEA})$	3.14	°C/W

8. Case temperature measured using thermocouple embedded in heat-sink. Contact local applications support team for more details on this measurement.

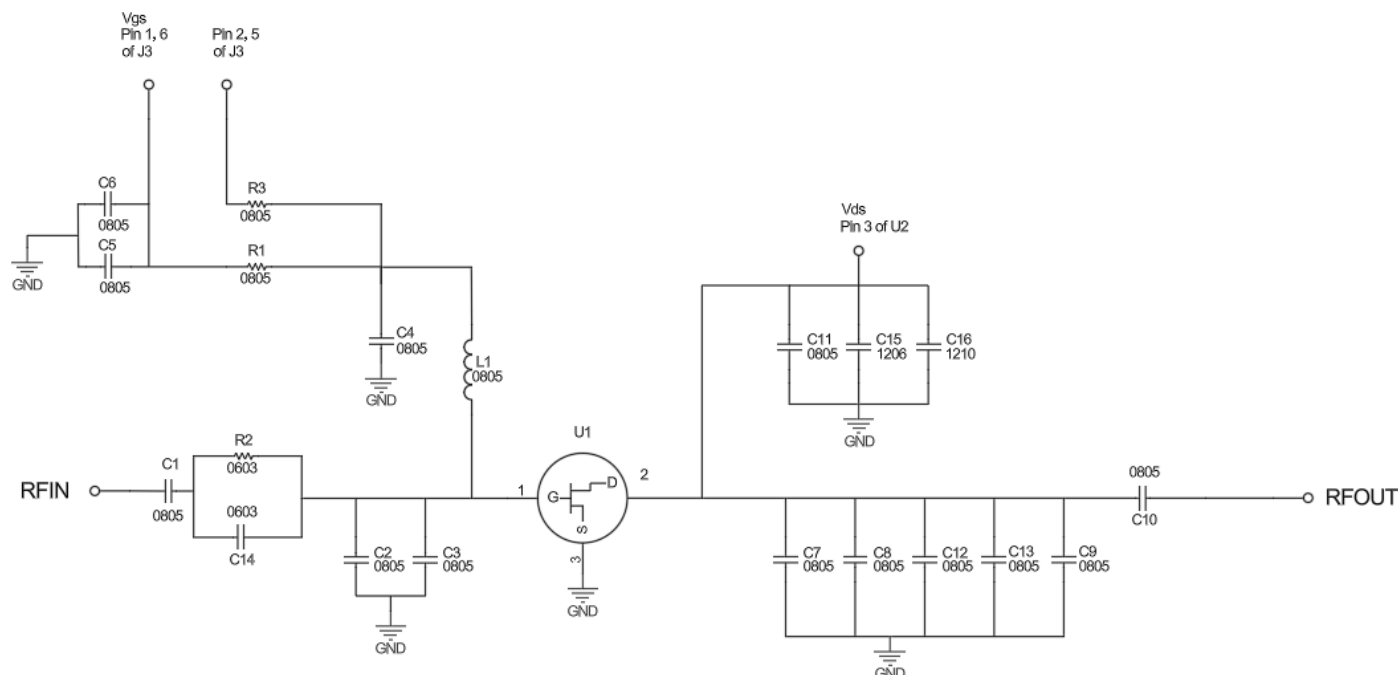
## Handling Procedures

Please observe the following precautions to avoid damage:

## Static Sensitivity

Gallium Nitride Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1B, CDM Class C3 devices.

## Application Fixture 2400 - 2500 MHz



### Description

Parts measured on application board (20-mil thick RF35A2). Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

### Bias Sequencing

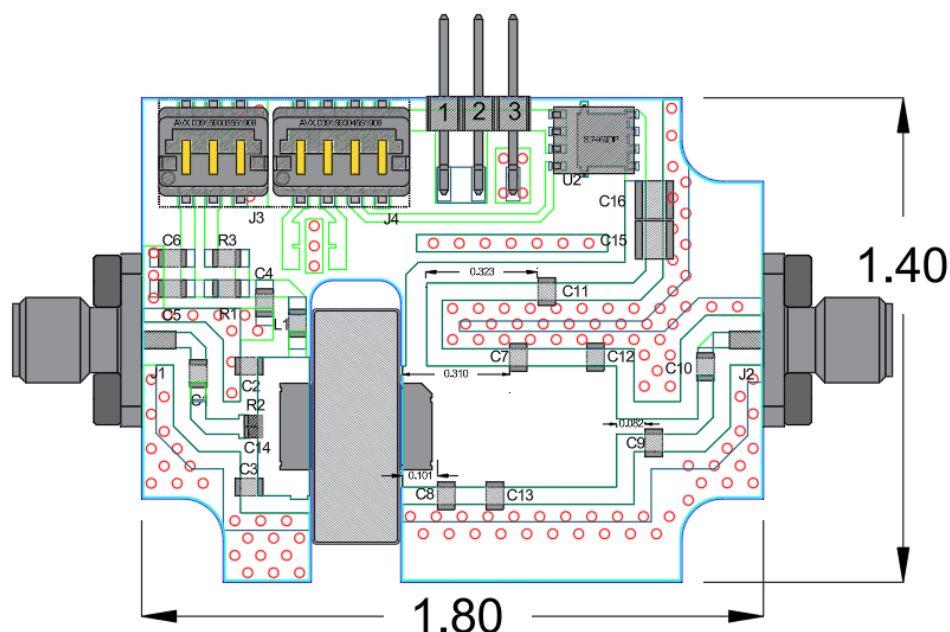
#### Turning the device ON

1. Set  $V_{GS}$  to pinch-off ( $V_P$ ).
2. Turn on  $V_{DS}$  to nominal voltage (50 V).
3. Increase  $V_{GS}$  until  $I_{DS}$  current is reached.
4. Apply RF power to desired level.

#### Turning the device OFF

1. Turn the RF power off.
2. Decrease  $V_{GS}$  down to  $V_P$  pinch-off.
3. Decrease  $V_{DS}$  down to 0 V.
4. Turn off  $V_{GS}$ .

Application Fixture 2400 - 2500 MHz

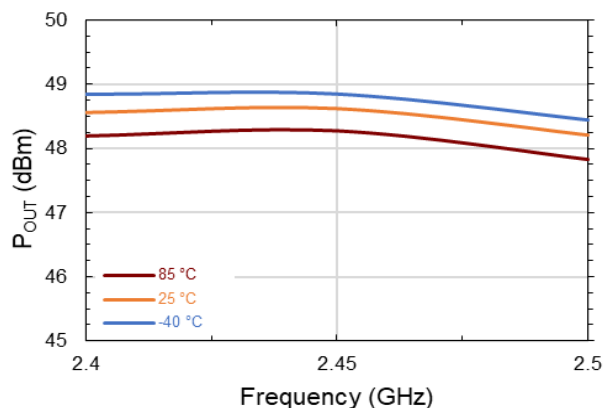


Parts List

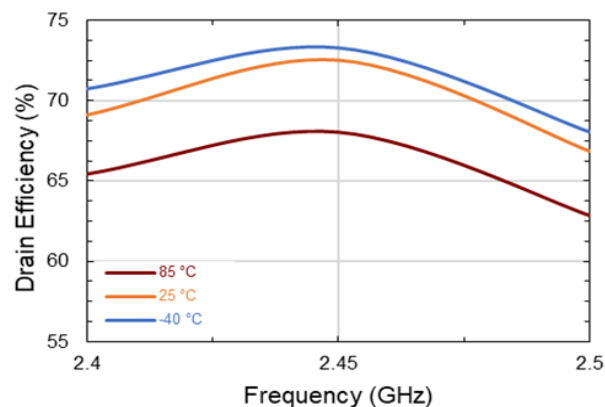
Reference Designator	Value	Tolerance	Manufacturer	Part Number
C1	22 pF	5%	Kyocera AVX	600F220JT250XT
C10	10 pF	5%	Kyocera AVX	600F100JT250XT
C11, C13	3 pF	0.1pF	Kyocera AVX	600F3R0BT250XT
C14	6.8 pF	0.1pF	Kyocera AVX	600S6R8BT250XT
C15	1 $\mu$ F	10%	Murata	GRM32ER72A105KA01
C16	10 $\mu$ F	10%	Murata	GRM32ER61H106KA12
C2, C3	1.1 pF	0.1pF	Kyocera AVX	600F1R1BT250XT
C4	4.7 pF	0.1pF	Kyocera AVX	600F4R7BT250XT
C5	0.01 $\mu$ F	0.01uF	Murata	GRM21BR72E103KW03
C6	1 $\mu$ F	10%	Murata	GCM21BC72A105KE36
C7, C8, C9, C12	1.8 pF	0.1pF	Kyocera AVX	600F1R8BT250XT
L1	12 nH	2%	Coilcraft	0805HP-12NXGRC
R1	5.1 $\Omega$	1%	Yageo	RC0805FR-075R1L
R2	5.6 $\Omega$	1%	Yageo	AC0603FR-075R6L
R3	1 k $\Omega$	5%	VIKING	CR-050FLF—1K
U2	80-V	-	MACOM	Si7469DP
Q1	50 W	-	MACOM	MAPC-A1110-AP
PCB	Taconnic RF35A2, 20 mil, 1 oz. Cu, Au Finish			

**Typical Performance Curves as Measured in the 2400 - 2500 MHz Application Fixture:**  
**CW, 2.45 GHz,  $V_{DS} = 50$  V,  $I_{DQ} = 100$  mA,  $T_C = 25^\circ\text{C}$**   
**Unless Otherwise Noted**

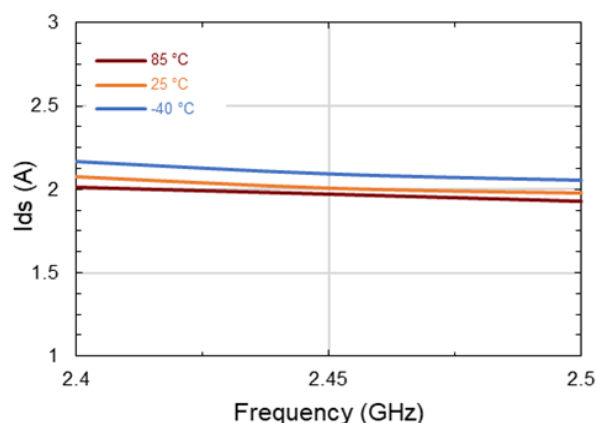
**Output Power vs. Temperature and Frequency**



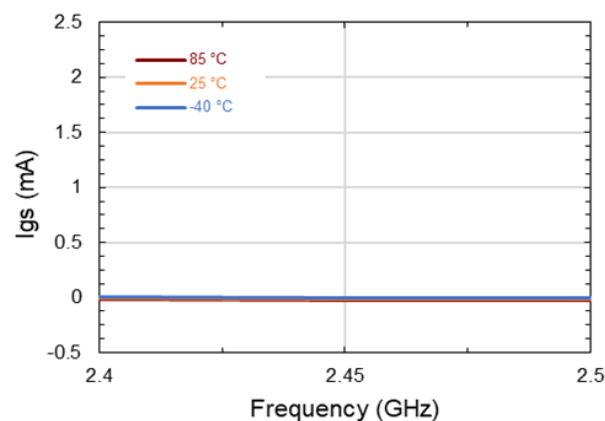
**Drain Efficiency vs. Temperature and Frequency**



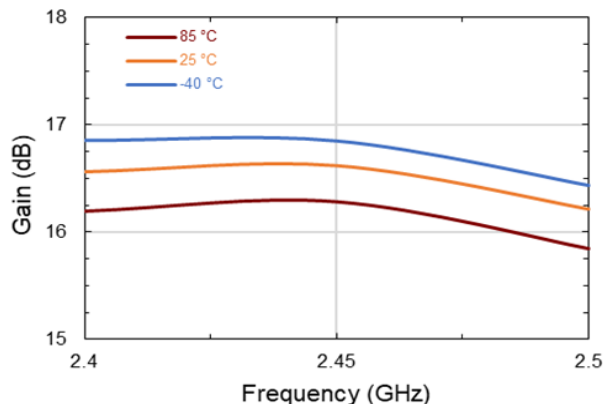
**Drain Current vs. Temperature and Frequency**



**Gate Current vs. Temperature and Frequency**

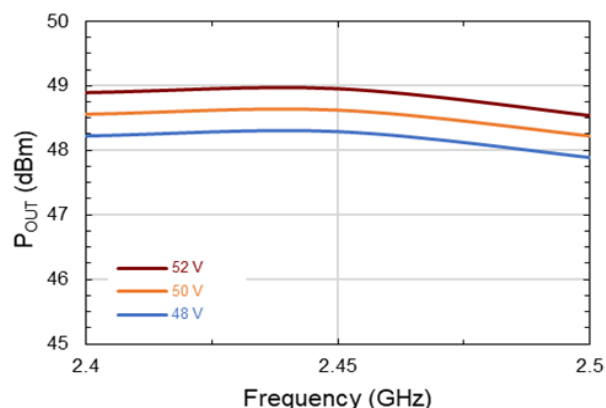


**Large Signal Gain vs. Temperature and Frequency**

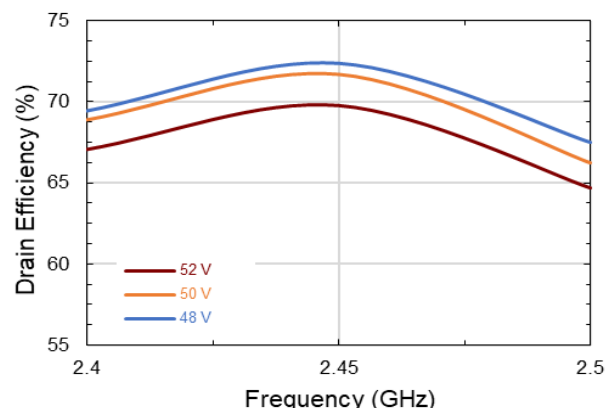


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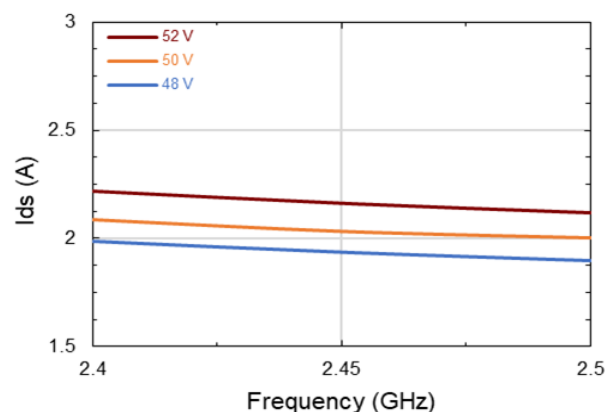
**Output Power vs.  $V_{DS}$  and Frequency**



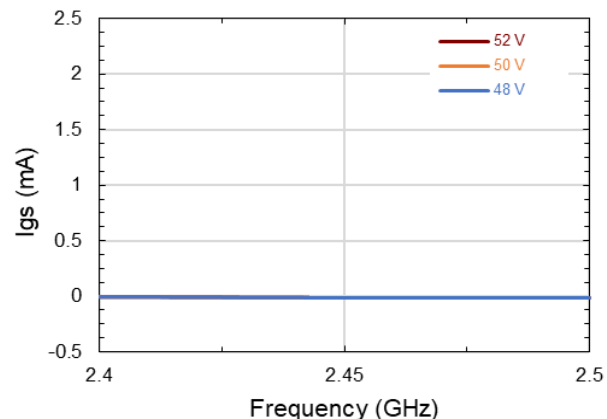
**Drain Efficiency vs.  $V_{DS}$  and Frequency**



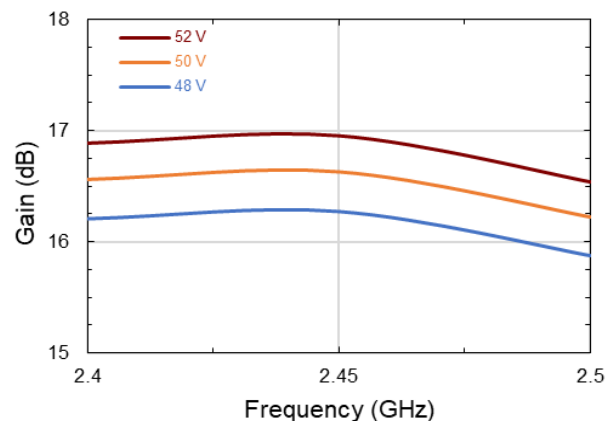
**Drain Current vs.  $V_{DS}$  and Frequency**



**Gate Current vs.  $V_{DS}$  and Frequency**

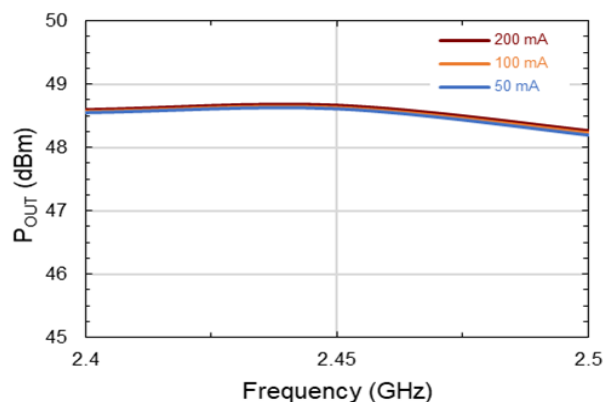


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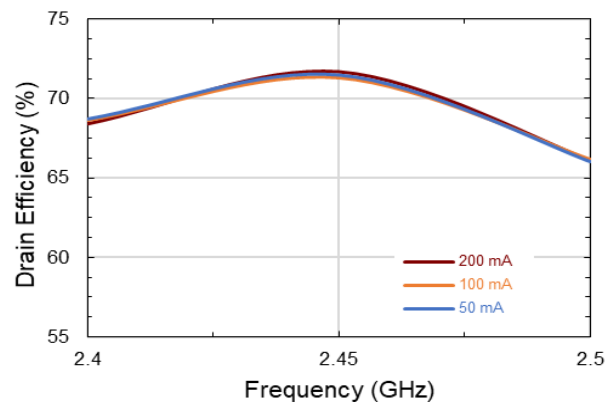


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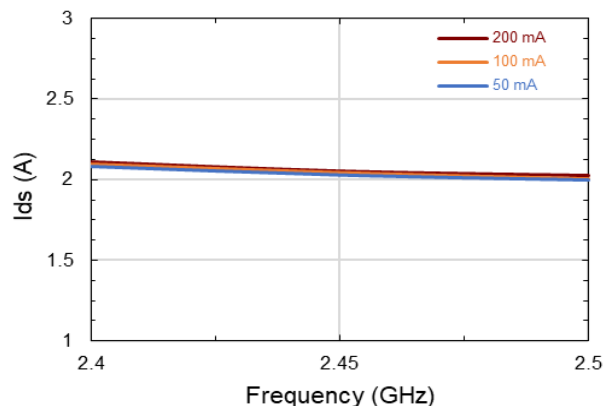
**Output Power vs.  $I_{DQ}$  and Frequency**



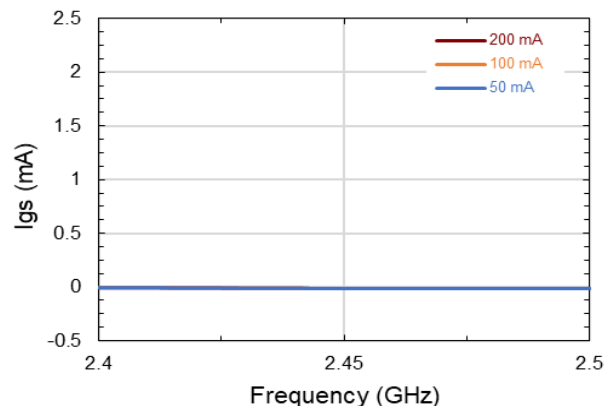
**Drain Efficiency vs.  $I_{DQ}$  and Frequency**



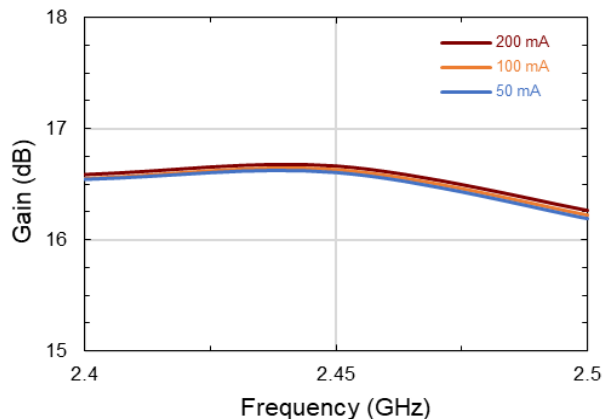
**Drain Current vs.  $I_{DQ}$  and Frequency**



**Gate Current vs.  $I_{DQ}$  and Frequency**



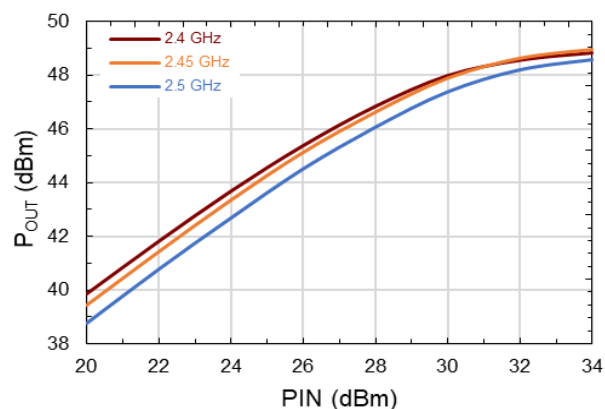
**Large Signal Gain vs.  $I_{DQ}$  and Frequency**



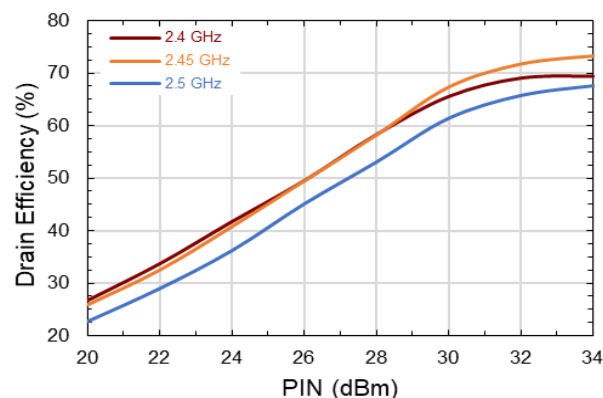


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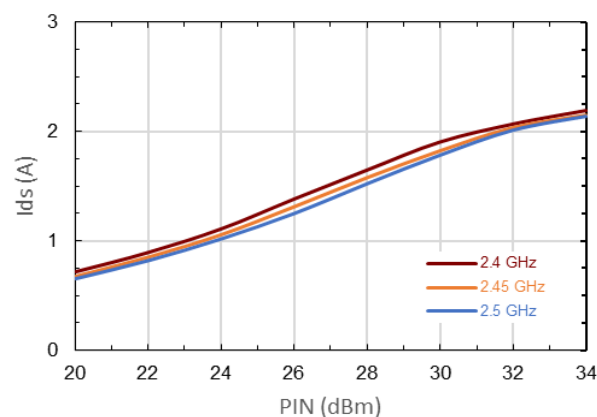
**Output Power vs. Frequency and  $P_{IN}$**



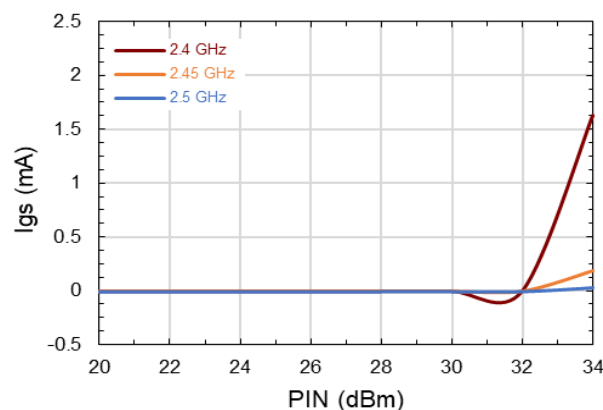
**Drain Efficiency vs. Frequency and  $P_{IN}$**



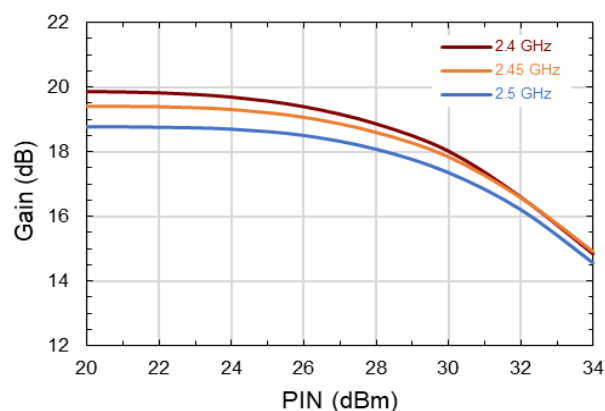
**Drain Current vs. Frequency and  $P_{IN}$**



**Gate Current vs. Frequency and  $P_{IN}$**

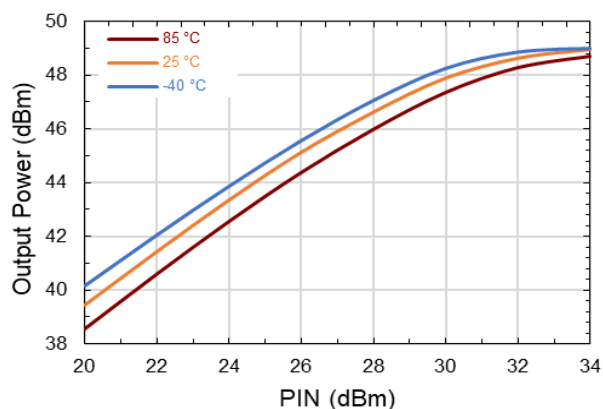


**Large Signal Gain vs. Frequency and  $P_{IN}$**

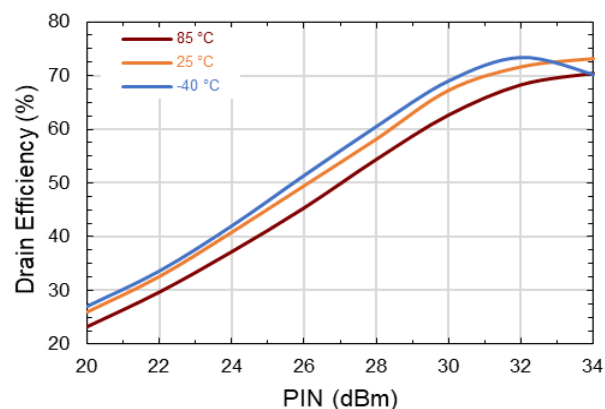


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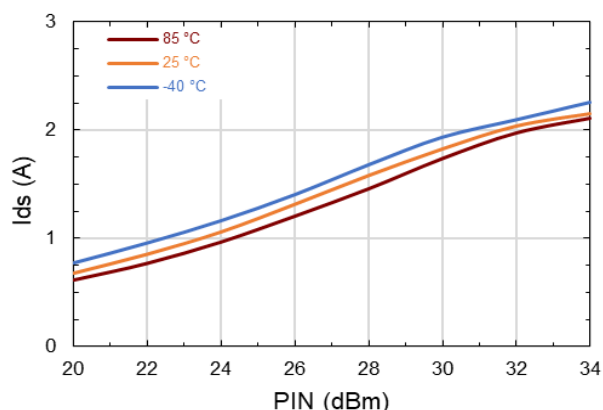
**Output Power vs. Temperature and  $P_{IN}$**



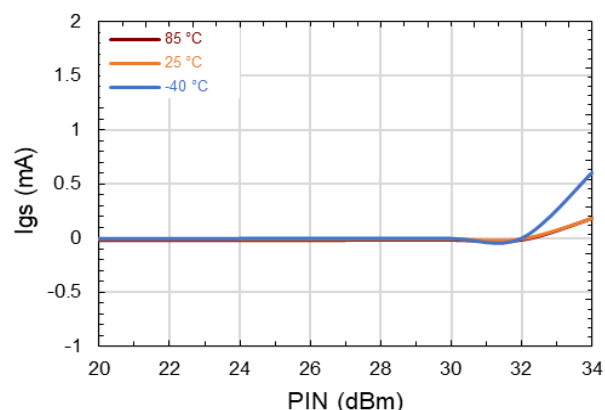
**Drain Efficiency vs. Temperature and  $P_{IN}$**



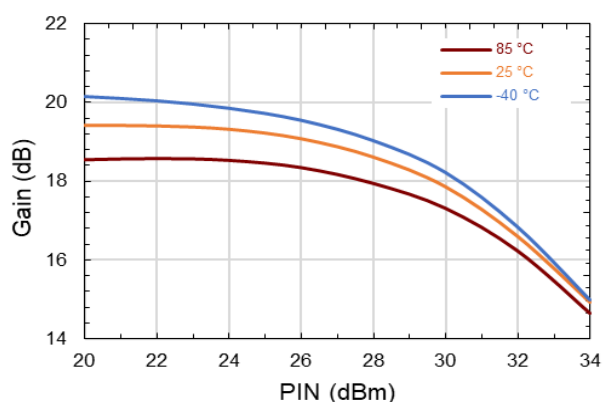
**Drain Current vs. Temperature and  $P_{IN}$**



**Gate Current vs. Temperature and  $P_{IN}$**

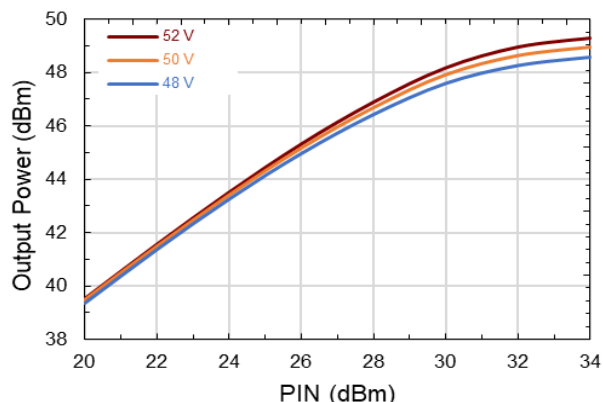


**Large Signal Gain vs. Temperature and  $P_{IN}$**

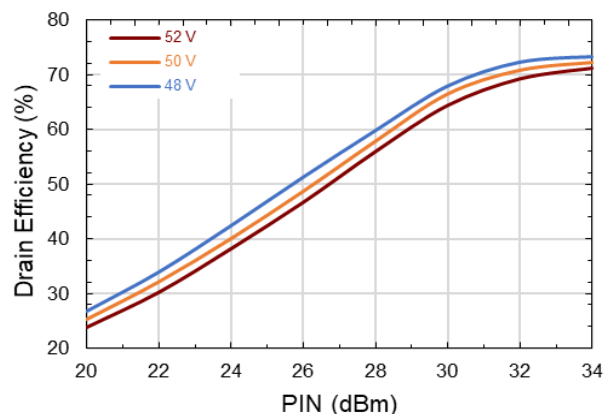


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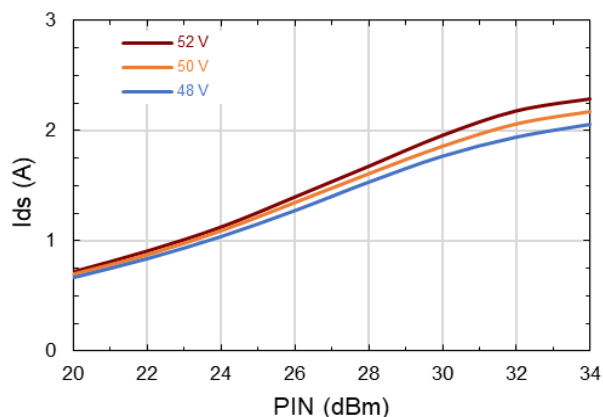
**Output Power vs.  $V_{DS}$  and  $P_{IN}$**



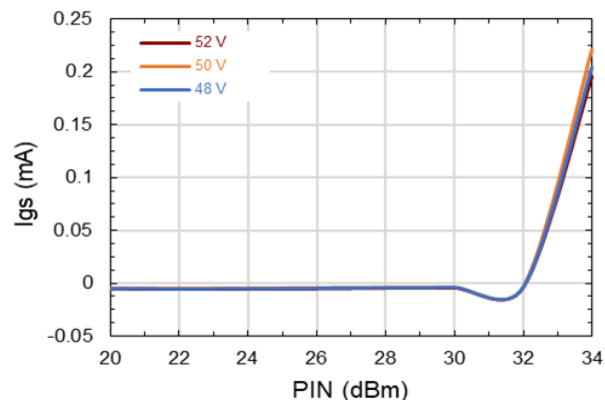
**Drain Efficiency vs.  $V_{DS}$  and  $P_{IN}$**



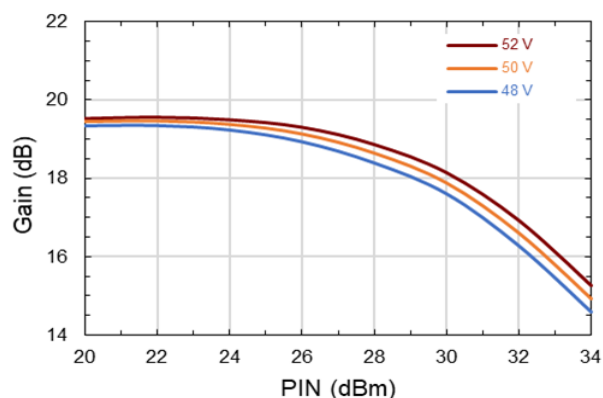
**Drain Current vs.  $V_{DS}$  and  $P_{IN}$**



**Gate Current vs.  $V_{DS}$  and  $P_{IN}$**

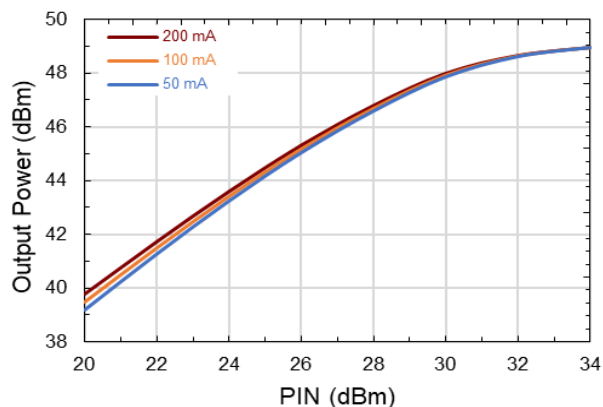


**Large Signal Gain vs.  $V_{DS}$  and  $P_{IN}$**

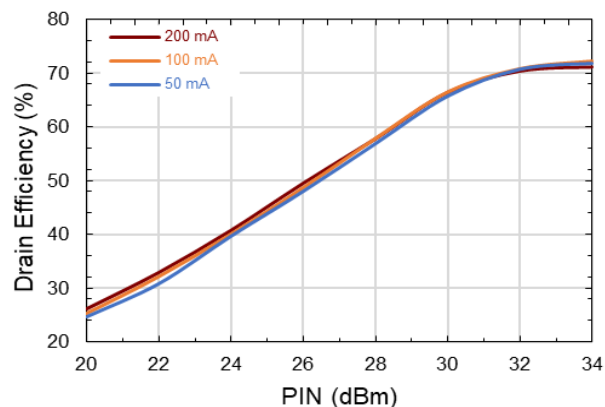


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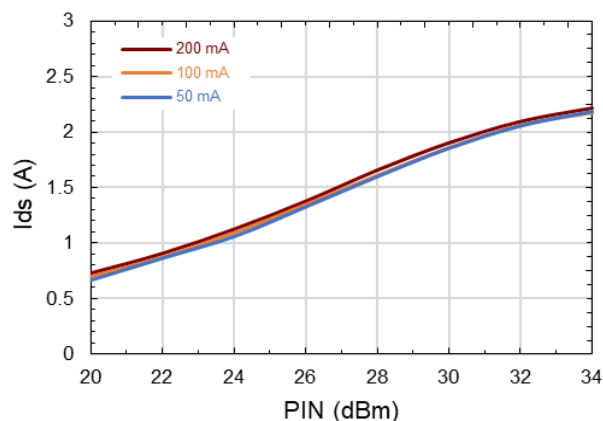
**Output Power vs.  $I_{DQ}$  and  $P_{IN}$**



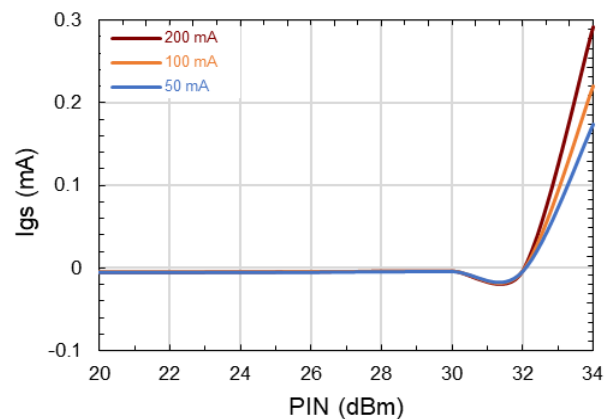
**Drain Efficiency vs.  $I_{DQ}$  and  $P_{IN}$**



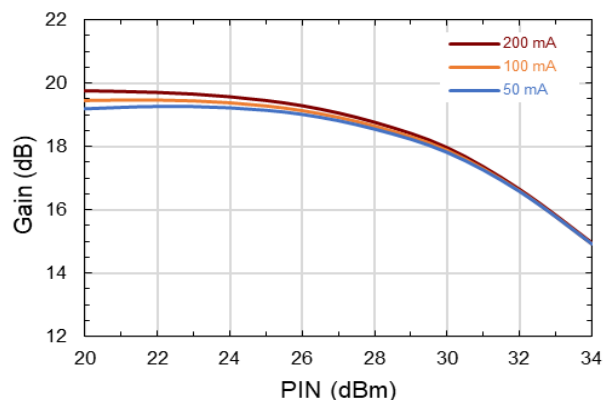
**Drain Current vs.  $I_{DQ}$  and  $P_{IN}$**



**Gate Current vs.  $I_{DQ}$  and  $P_{IN}$**

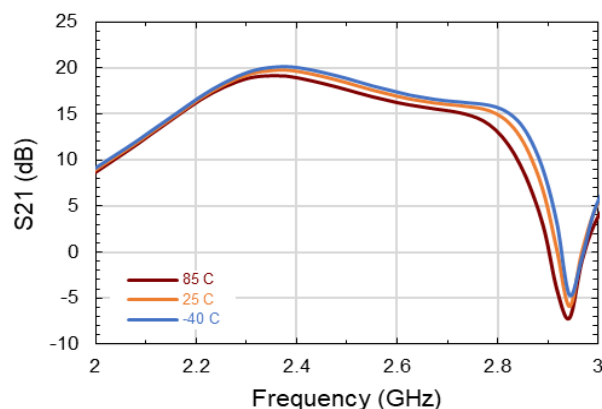


**Large Signal Gain vs.  $I_{DQ}$  and  $P_{IN}$**

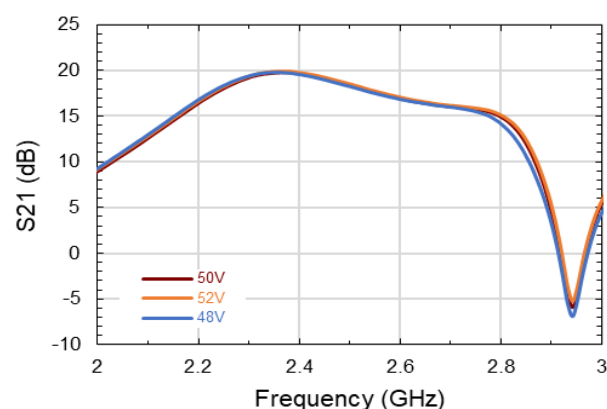


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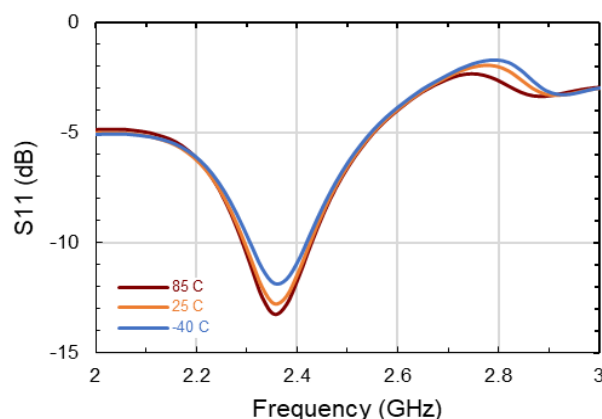
***S21 vs Frequency and Temperature***



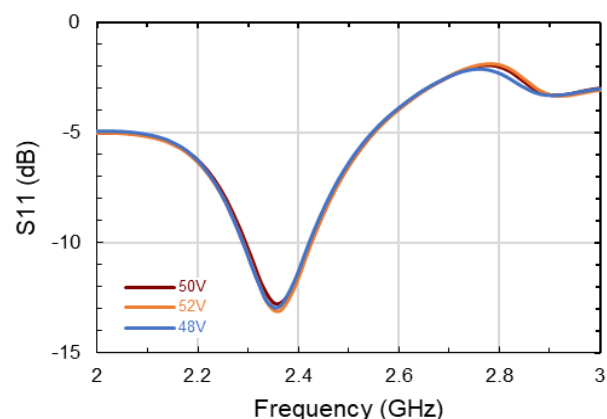
***S21 vs Frequency and  $V_{DS}$***



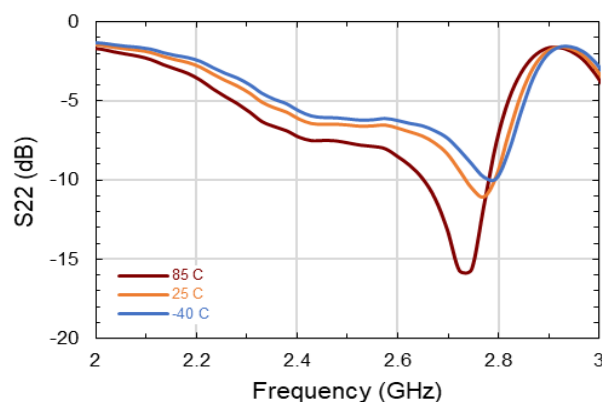
***S11 vs Frequency and Temperature***



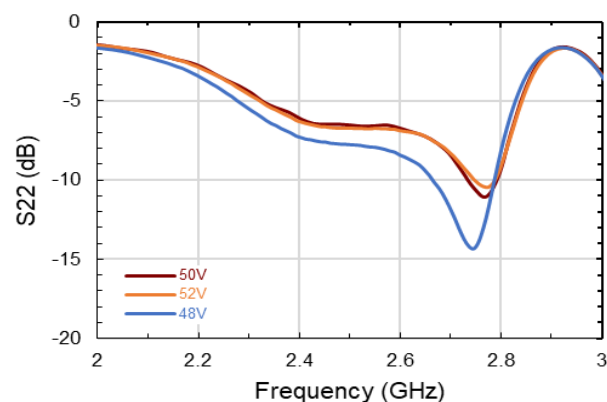
***S11 vs Frequency and  $V_{DS}$***



***S22 vs Frequency and Temperature***

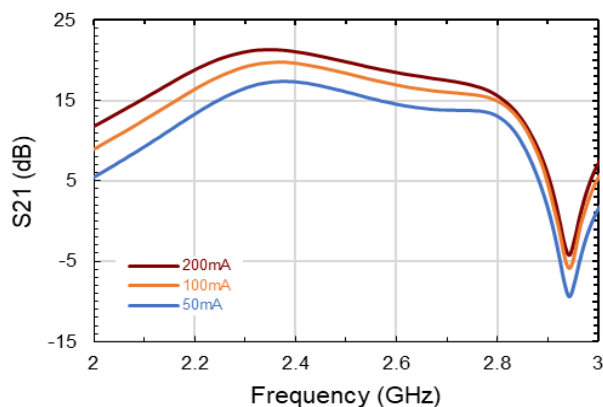


***S22 vs Frequency and  $V_{DS}$***

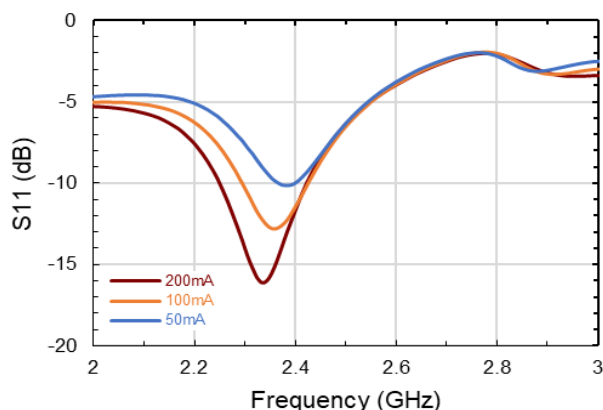


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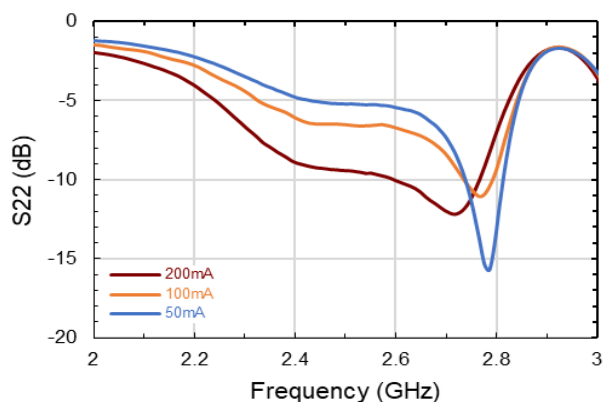
***S21 vs Frequency and  $I_{DQ}$***



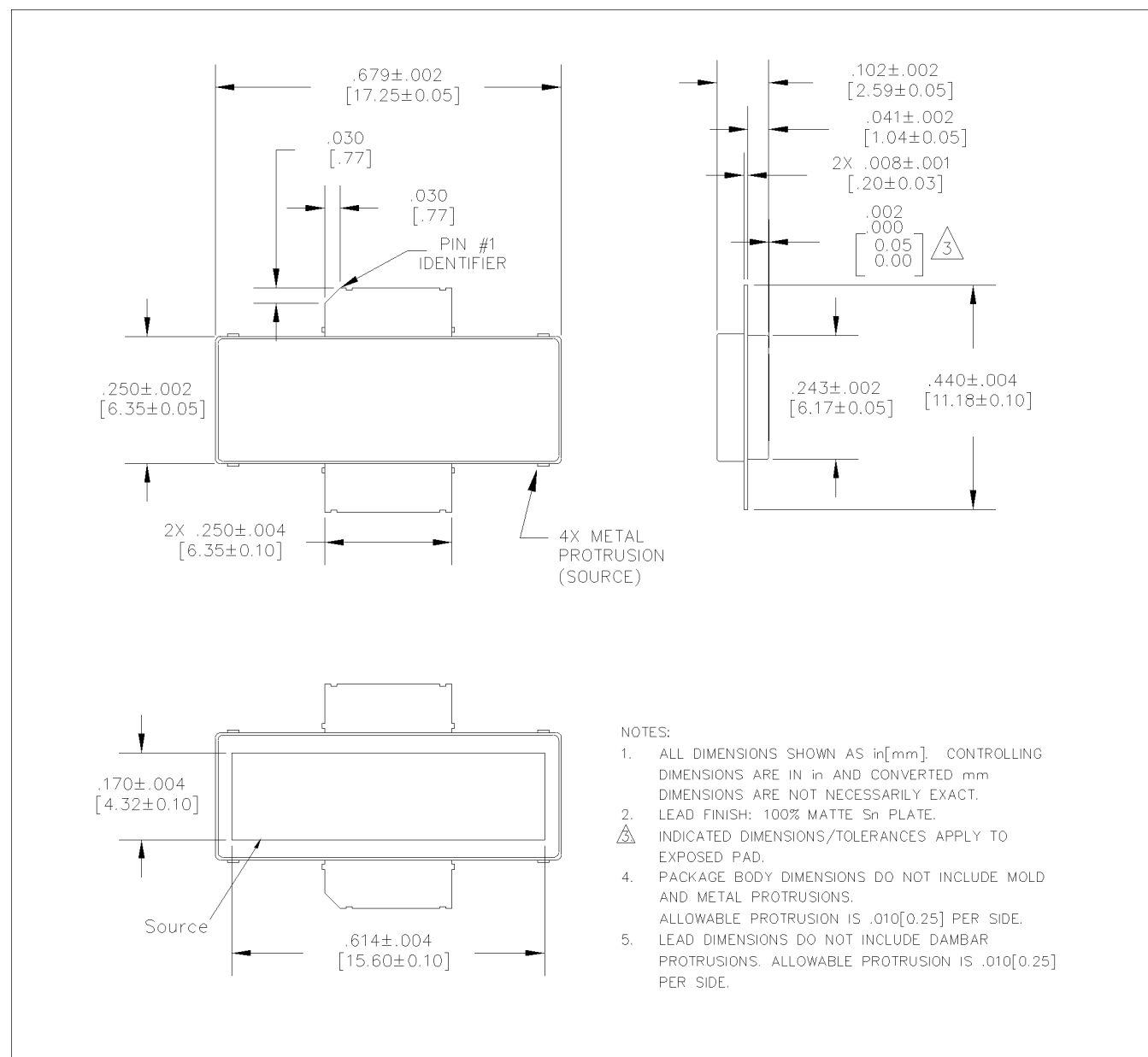
***S11 vs Frequency and  $I_{DQ}$***



***S22 vs Frequency and  $I_{DQ}$***



# Lead-Free TO-272S-2 Package Dimensions†



† Reference Application Note AN0004125 for lead-free solder reflow recommendations.  
Meets JEDEC moisture sensitivity level 3 requirements.  
Plating is Matte Sn.

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